XP232N0301TR-G

N-channel MOSFET 30V, 0.3A

ETR11042-001a

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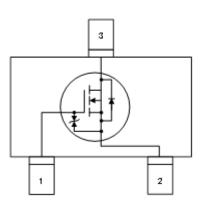


On-State Resistance Driving voltage

: R_{DS}(on)=2.0Ω @V_{GS} =10V : 4.5V Environmentally Friendly : EU RoHS Compliant, Pb Free

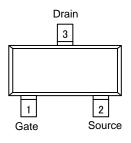


■EQUIVALENT CIRCUIT



■PIN CONFIGURATION

●SOT-23(TO-236)



PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT	
XP232N0301TR-G *	SOT-23(TO-236)	3,000 pcs/ Reel	

* The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant

■ABSOLUTE MAXIMUM RATINGS

			Ta=25°C
PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (DC)	lD	0.3	A
Drain Current(Pulse) (*1)	IDP	0.6	A
Channel Power Dissipation (*2)	Pd	0.4	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

 $^{(^*1)}\mathsf{PW}\!\leq\!10\mu s,duty\ cycle\!\leq\!1\%$

(*2)When implemented on a PCB defined by JESD51-7

XP232N0301TR-G ELECTRICAL CHARACTERISTICS

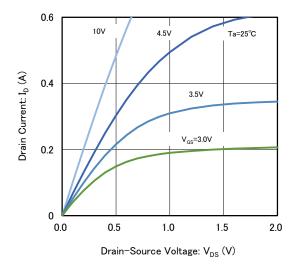
						Ta=25℃
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 250µA, V _{GS} = 0V	30	-	-	V
Drain-Source Leakage Current	I _{DSS}	V_{DS} = 30V, V_{GS} = 0V	-	-	1	μA
Gate-Source Leakage Current	I _{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±10	μA
Gate Threshold Voltage	V _{GS(off)}	I _D = 250uA, V _{DS} = V _{GS}	0.9	1.7	2.5	V
Drain-Source On Resistance	Р	V _{GS} = 10V, I _D = 100mA	-	1.0	2.0	Ω
Drain-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 100mA	-	1.7	2.5	Ω
Input Capacitance	Ciss	V _{DS} = 10V, V _{GS} = 0V f= 1MHz	-	22	-	pF
Output Capacitance	Coss		-	9	-	pF
Reverse Transfer Capacitance	Crss		-	2.5	-	pF
Turn-on Delay Time	t _{d(on)}		-	10	-	ns
Rise Time	tr	V_{DD} = 10V, I_{D} = 100mA	-	4	-	ns
Turn-off Delay Time	t _{d(off)}	V _{GS} = 10V	-	30	-	ns
Fall Time	t _f		-	10	-	ns
Total Gate Charge	Qg		-	0.36	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} = 10V, I_{D} = 150mA	-	0.06	-	nC
Gate-Drain Charge	Q _{gd}	- V _{GS} = 10V	-	0.1	-	nC
Diode Forward Voltage	V _{SD}	I _S = 100mA, V _{GS} = 0V	-	0.7	1.1	V

■NOTES ON USE

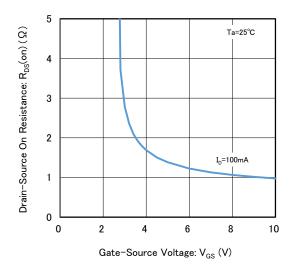
- Please use this IC within the absolute maximum ratings. Even within the ratings, in case of high load use continuously such as high temperature, high voltage, high current and thermal stress may cause reliability degradation of the IC.
- Torex places an importance on improving our products and their reliability.
 We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

■TYPICAL PERFORMANCE CHARACTERISTICS

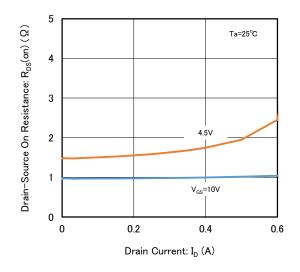
(1) Drain Current vs. Drain-Source Voltage



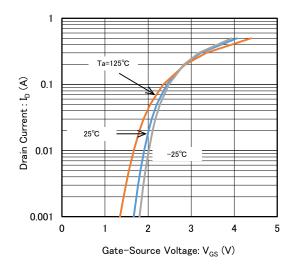
(3) Drain-Source On Resistance vs. Gate-Source Voltage



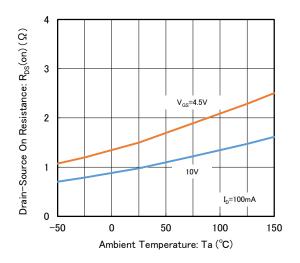
(5) Drain-Source On Resistance vs. Drain Current



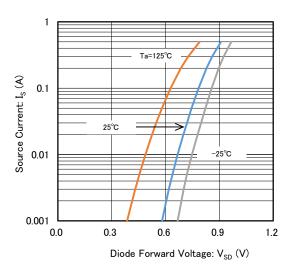
(2) Drain Current vs. Gate-Source Voltage



(4) Drain-Source On Resistance vs. Ambient Temperature



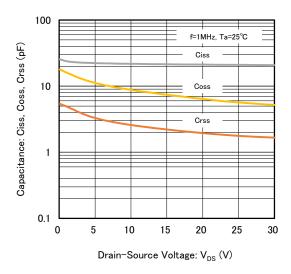
(6) Source Current vs. Diode Forward Voltage



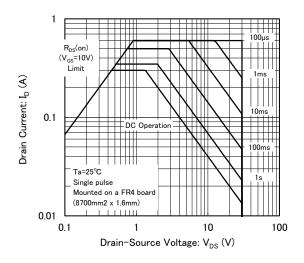
XP232N0301TR-G

■TYPICAL PERFORMANCE CHARACTERISTICS

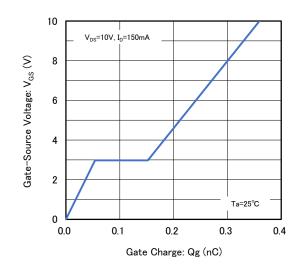
(7) Ciss, Coss, Crss vs. Drain-Source Voltage



(9) Area of Safe Operation



(8) Gate-Source Voltage vs. Gate Charge



■ PACKAGING INFORMATION

For the latest package information go to, www.torexsemi.com/technical-support/packages

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS	
SOT-23(TO-236)	<u>SOT-23(TO-236) PKG</u>	JESD51-7 Board	SOT-23(TO-236) PowerDissipation

■MARKING RULE

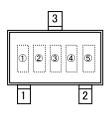
●SOT-23(TO-236)

① ②, ③represents product series

MARK			PRODUCT SERIES
1	2	3	PRODUCT SERIES
3	2	Ν	XP232N0301**-G

④, ⑤ represents production lot number
01 to 09, 0A to 0Z, 11 to 9Z, A1 to A9, AA to AZ, B1 to ZZ repeated
(G, I, J, O, Q, W excluded)
*No character inversion used

SOT-23(TO-236)



XP232N0301TR-G

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